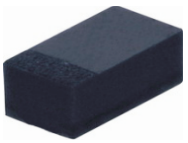
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBER40 (RoHs Device)

Io = 200 mA
V_R = 40 Volts



Features

- Low reverse current.
- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Majority carrier conduction.

Mechanical data

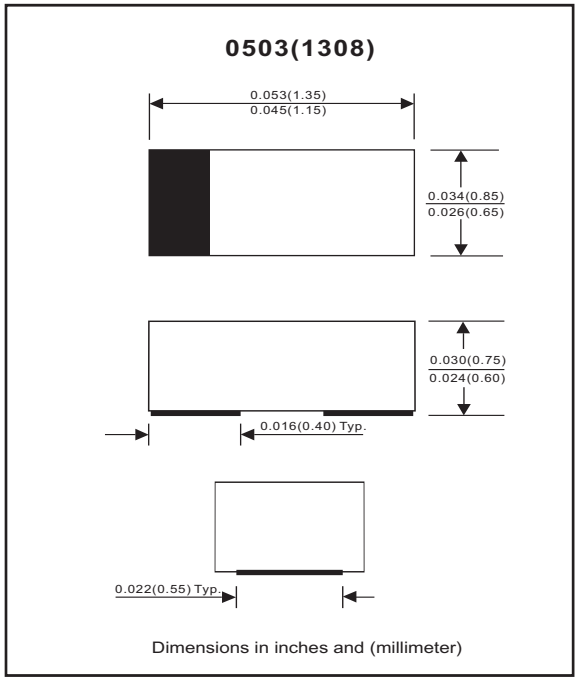
Case: 0503(1308) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.002 gram(approx.).



Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Peak reverse voltage		V_{RM}			40	V
Reverse voltage		V_R			40	V
RMS reverse voltage		$V_{R(RMS)}$			28	V
Average forward rectified current		I_O			200	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}			0.6	A
Power dissipation		P_D			150	mW
Storage temperature		T_{STG}	-65		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 1mA I_F = 40mA	V_F			0.381	V
Reverse current	V_R = 30V	I_R			0.2	uA
Capacitance between terminals	f = 1 MHz, and 0 VDC reverse voltage	C_T			5	pF
Reverse recovery time	I_F=I_R=10mA,Irr=0.1xIR,RL=100 ohm	T_{rr}			5	nS

RATING AND CHARACTERISTIC CURVES (CDBER40)

Fig. 1 - Forward characteristics

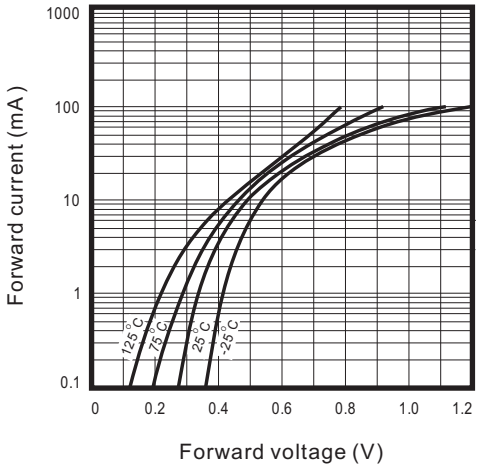


Fig. 2 - Reverse characteristics

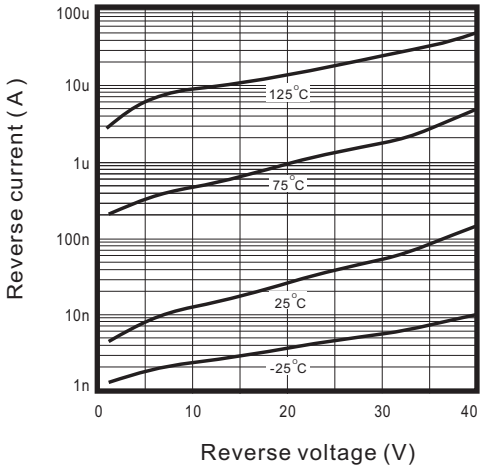


Fig.3 - Capacitance between terminals characteristics

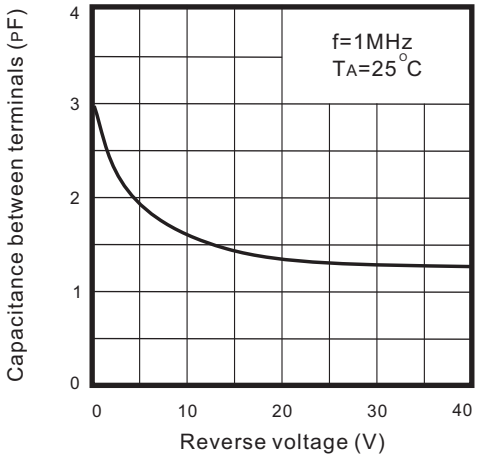


Fig.4 - Current derating curve